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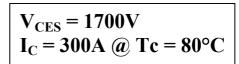


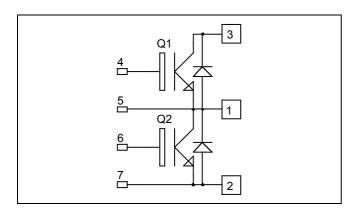






Phase leg Trench + Field Stop IGBT3 Power Module





Application

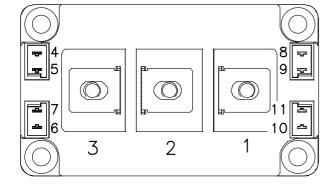
- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors



- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant



Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1700	V
$I_{\rm C}$	Continuous Collector Current	$T_C = 25^{\circ}C$	400	
	Continuous Conector Current	$T_C = 80$ °C	300	A
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	600	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25$ °C	1470	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125$ °C	600A@1650V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1700V$				3	mA
V _{CE(on)}	Collector Emitter on Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		2.0	2.5	V
		$I_C = 300A$ $T_j = 125^{\circ}C$	$T_j = 125$ °C		2.4		·
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 12 \text{ mA}$		5.2	5.8	6.4	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics

•	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V, V_{CE} = 25V$			27		nF
C_{res}	Reverse Transfer Capacitance	f = 1MHz			0.9		ШГ
Q_{G}	Gate charge	V _{GE} =±15V, I _C =300A V _{CE} =900V			3.5		μС
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ((25°C)		280		ns
T _r	Rise Time	$V_{GE} = \pm 15V$	=		80		
T _{d(off)}	Turn-off Delay Time	$V_{\text{Bus}} = 900V$ $I_{\text{C}} = 300A$	-		850		
T_{f}	Fall Time	$R_G = 4.7\Omega$		120			
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching (125°C) $V_{GE} = \pm 15V$		300		
$T_{\rm r}$	Rise Time				100		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 900V$ $I_C = 300A$	-		1000		ns
T_{f}	Fall Time	$R_G = 4.7\Omega$	C		200		
Е	Turn On Engrav	$V_{GE} = \pm 15V$ T_1	= 25°C		71		
Eon	Turn On Energy	$V_{\text{Bus}} = 900V$ $T_{\text{j}} =$	= 125°C		105		mJ
E_{off}	Turn Off Energy		= 25°C		64		1113
Loff	Turn On Energy	$R_G = 4.7\Omega$ $T_i =$	= 125°C		94		
I_{sc}	Short Circuit data	$V_{GE} \le 15V$; $V_{Bus} = 1000V$ $t_p \le 10 \mu s$; $T_i = 125 ^{\circ}C$			1200		A

Reverse diode ratings and characteristics

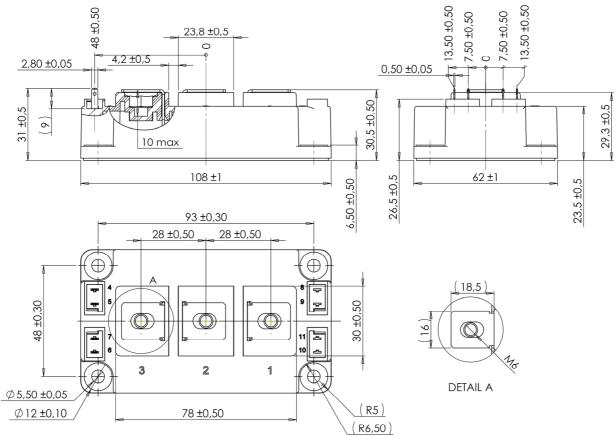
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1700			V
Ţ	Maximum Reverse Leakage Current	V _R =1700V	$T_j = 25^{\circ}C$			750	^
I_{RRM}			$T_j = 125$ °C			1000	μΑ
I_F	DC Forward Current		$Tc = 80^{\circ}C$		300		A
V_{F}	Diode Forward Voltage	$I_F = 300A$	$T_j = 25$ °C		1.8	2.2	V
V _F			$T_i = 125$ °C		1.9		
+	Reverse Recovery Time	$I_F = 300A$ $V_R = 900V$ $di/dt = 3500A/\mu s$	$T_j = 25^{\circ}C$		385		ng
t_{rr}			$T_j = 125$ °C		490		ns
0	Reverse Recovery Charge		$T_j = 25^{\circ}C$		76		C
Q_{rr}			$T_{j} = 125^{\circ}C$		124		μС
E_{rr}	Reverse Recovery Energy	·	$T_j = 25^{\circ}C$		35		mJ
L _{II} I			$T_j = 125$ °C		70	·	1113



Thermal and package characteristics

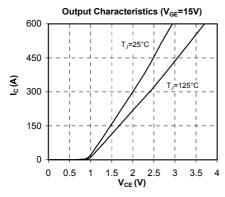
Symbol	Characteristic			Min	Тур	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.085	°C/W
KthJC			Diode			0.13	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range	perating junction temperature range -40 150				150	
T_{STG}	Storage Temperature Range Operating Case Temperature			-40		125	°C
T_{C}				-40		125	
Torque	Mounting torque	For terminals	M6	3		5	N.m
		To Heatsink	M6	3		5	18.111
Wt	Package Weight	_				350	g

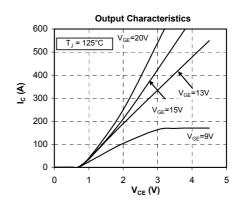
D3 Package outline (dimensions in mm)

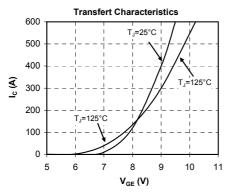


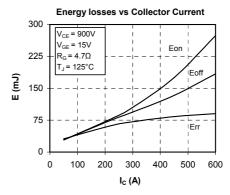


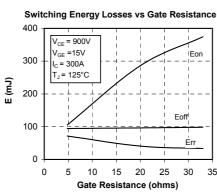
Typical Performance Curve

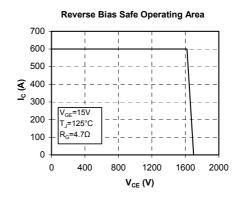


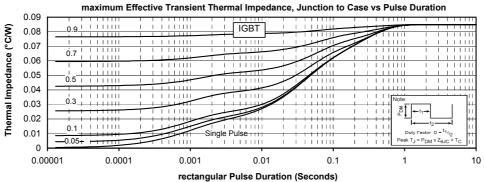




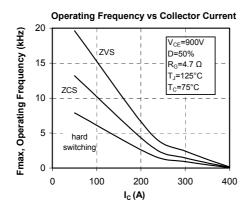


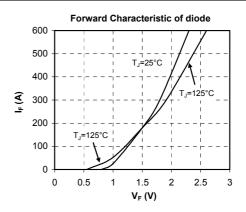


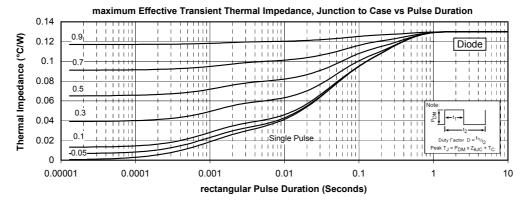














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